

Silicon Power Transistors

2SC2246

DESCRIPTION

- High voltage ,high speed
- With TO-3 package

APPLICATIONS

- Power switching
- Power amplification
- power driver

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

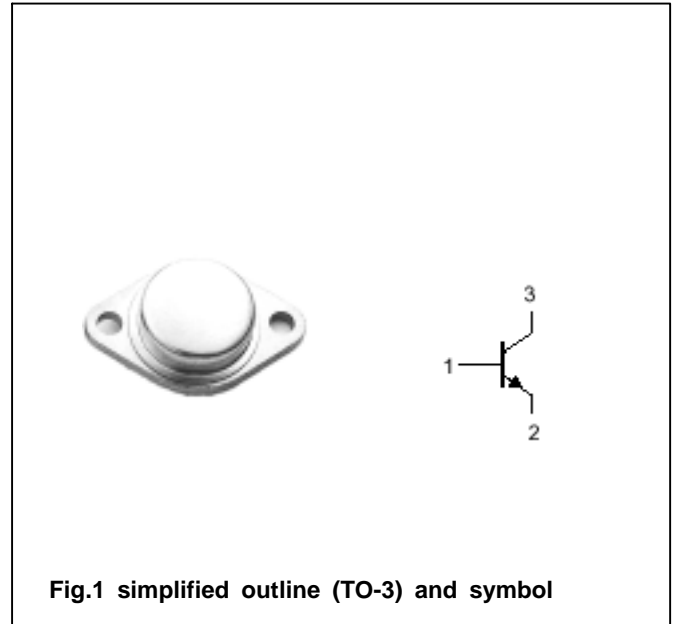


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CB0}	Collector-base voltage	Open emitter	450	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _{CM}	Collector current-Peak		30	A
I _B	Base current		6	A
P _T	Total power dissipation	T _{mb} =25	100	W
T _j	Junction temperature		200	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-mb}	Thermal resistance from junction to mounting base	1.0	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; L=25mH	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A I _B =1.2A			1.2	V
V _{Besat}	Base-emitter saturation voltage	I _C =6A I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =450V I _E =0 T _C =125			1 4	mA
I _{CEO}	Collector cut-off current	V _{CE} =400V I _B =0			5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =6A ; V _{CE} =5V	10			

Switching times

t _{on}	Turn-on time	I _C =6A I _{B1} =- I _{B2} =1.2A			1.0	μs
t _s	Storage time				2.0	μs
t _f	Fall time				1.0	μs

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PACKAGE OUTLINE

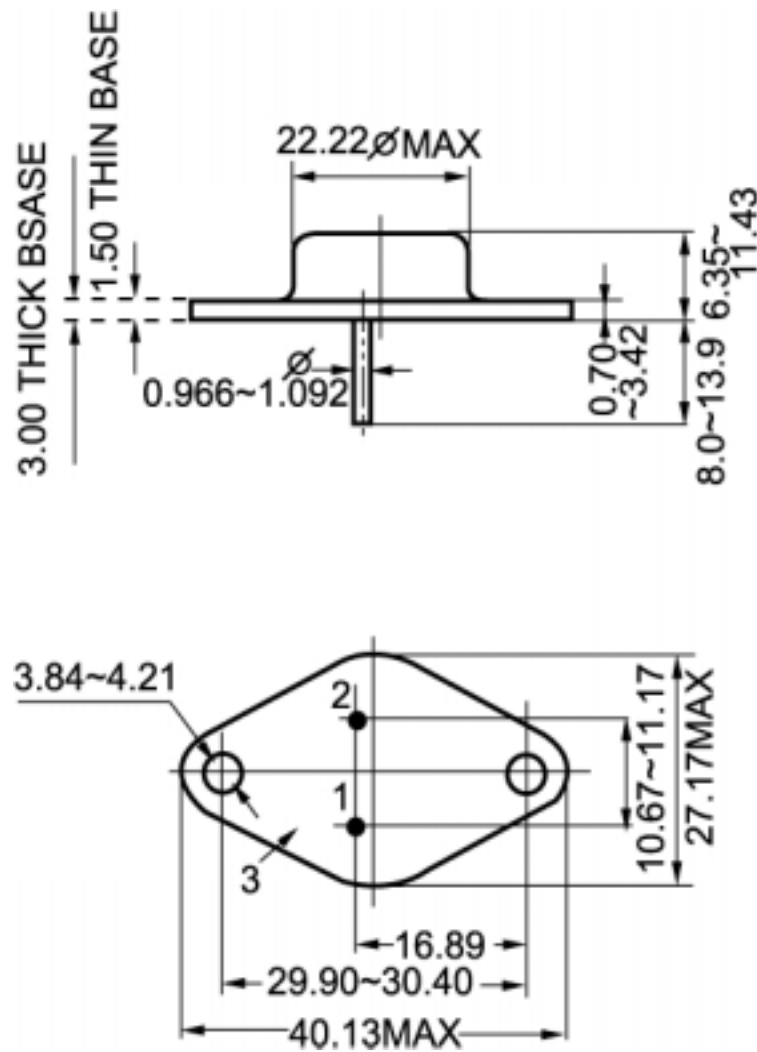


Fig.2 Outline dimensions